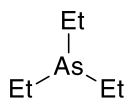


Catalog # 33-3400 Triethylarsine, 99%



## Thermal Behavior:

- Melting point: -91°C
- Boiling point: 140°C

## Technical Notes:

1. ALD/CVD precursor for arsenic thin film deposition

Target Deposit	Deposition Technique	Delivery Temperature	Pressure	Co-reactants	Deposition Temperature	Ref.
GaAs	CVD	-	30-45 Torr	Me <sub>3</sub> Ga, H <sub>2</sub>	470-485°C	1

## References:

1. [J. Cryst. Growth, 1991, 115, 353](#)